

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

2SK3067

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

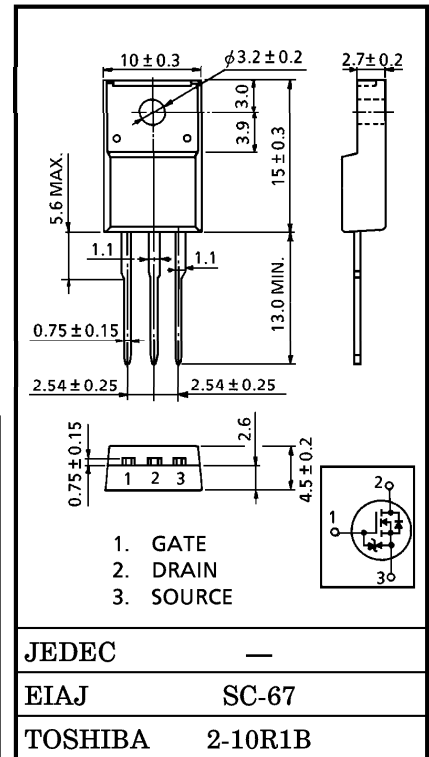
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 4.2 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 1.7 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu A$ (Max.) ($V_{DS} = 600 V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0 V$ ($V_{DS} = 10 V, I_D = 1 mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Drain-Gate Voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	DC	I_D	2	A
	Pulse ($t = 1 ms$)	I_{DP}	5	A
	Pulse ($t = 100 \mu s$)	I_{DP}	8	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	25	W
Single Pulse Avalanche Energy**		E_{AS}	93	mJ
Avalanche Current		I_{AR}	2	A
Repetitive Avalanche Energy*		E_{AR}	2.5	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	5.0	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C / W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90 V, T_{ch} = 25^\circ C$ (initial), $L = 41 mH, R_G = 25 \Omega, I_{AR} = 2 A$

This transistor is an electrostatic sensitive device. Please handle with caution.

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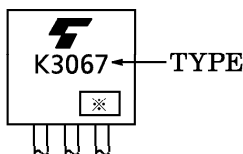
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	—	—	±10	μA	
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = ±10 μA, V _{DS} = 0 V	±30	—	—	V	
Drain Cut-off Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	—	—	100	μA	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	—	—	V	
Gate Threshold Voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	—	4.0	V	
Drain-Source ON Resistance	R _{D(S)ON}	V _{GS} = 10 V, I _D = 1 A	—	4.2	5.0	Ω	
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1 A	0.8	1.7	—	S	
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	380	—	pF	
Reverse Transfer Capacitance	C _{rss}		—	40	—		
Output Capacitance	C _{oss}		—	120	—		
Switching Time	Rise Time	t _r		—	15	—	ns
	Turn-on Time	t _{on}		—	25	—	
	Fall Time	t _f		—	20	—	
	Turn-off Time	t _{off}		V _{IN} : t _r , t _f < 5 ns, V _{DD} ≐ 200 V Duty ≦ 1%, t _w = 10 μs	—	80	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	V _{DD} ≐ 480 V, V _{GS} = 10 V, I _D = 2 A	—	9	—	nC	
Gate-Source Charge	Q _{gs}	—	—	5	—		
Gate-Drain ("Miller") Charge	Q _{gd}	—	—	4	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I _{DR}	—	—	—	2	A
Pulse Drain Reverse Current	I _{DRP}	t = 1 ms	—	—	5	A
	I _{DRP}	t = 100 μs	—	—	8	A
Diode Forward Voltage	V _{DSF}	I _{DR} = 2 A, V _{GS} = 0 V	—	—	-1.5	V
Reverse Recovery Time	t _{rr}	I _{DR} = 2 A, V _{GS} = 0 V	—	1000	—	ns
Reverse Recovery Charge	Q _{rr}	dI _{DR} / dt = 100 A / μs	—	5.0	—	μC

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)